

BC635/637/639

Switching and Amplifier Applications •Complement to BC636/638/640



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T=25C unless otherwise noted

Symbol	Parameter	Value	Units
V CER	Collector-Emitter Voltage at RBE=1KΩ		
	: BC635	45	V
	: BC637	60	V
	: BC639	100	V
VCES	Collector-Emitter Voltage		
	: BC635	45	V
	: BC637	60	V
	: BC639	100	V
VCEO	Collector-Emitter Voltage		
	: BC635	45	V
	: BC <mark>637</mark>	60	V
	: BC639	80	V
¥ _{BO}	Emitter-Base Voltage	5	V
I _C	Collector Current	1	Α
I _{CP}	Peak Collector Current	1.5	Α
	Base Current	100	mA
P C	Collector Power Dissipation	1	W
T 	Junqtion Temperature	150	°C
7	Storage Temperature	-65 ~ 150	°C
			I

[•] PW=5ms, Duty Cycle=10%

Electrical Characteristics noted

Symbol	ParameterTest Condition		Min.	Тур.	Max.	Units
BV C EO	Collector-Emitter Breakdown Voltagel	=10mA, IB=0				
DV C LO	: BC635		45			V
	: BC637		60			V
	: BC639		80			V
I _{CBO}	Collector Cut-off CurrentVCB=30V, IE=0				0.1	μΑ
I _{EBO}	Emitter Cut-off CurrentVEB=5V, IC=0				0.1	μΑ
h FE1	DC Current Gain : AllVCE=2V, IC=5mA		25			
hE2	: BC635VCE=2V, IC=150mA		40		25	
1 62	: BC637/BC639		40			
ի _{E3}	: AllVCE=2V, IC=500mA		25		0	
CE (sat)	Collector-Emitter Saturation VoltageIC	=500mA, IB=50mA			გ6	V
BE (on)	Base-Emitter On VoltageVCE=2V, IC=50	0mA				V
f _T	Current Gain Bandwidth ProductVCE= f=50MHz	SV, IC=10mA,		100	0.5 1	MHz

Typical Characteristics

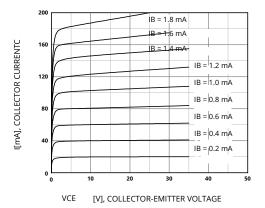


Figure 1. Static Characteristic

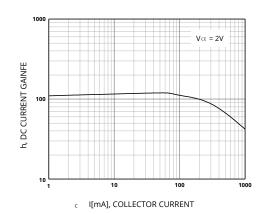


Figure 2. DC current Gain

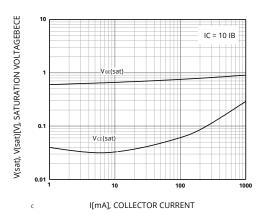


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

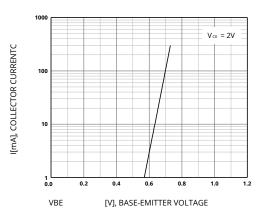


Figure 4. Base-Emitter On Voltage

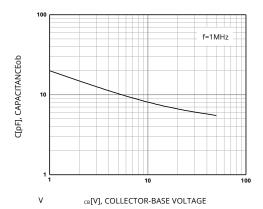
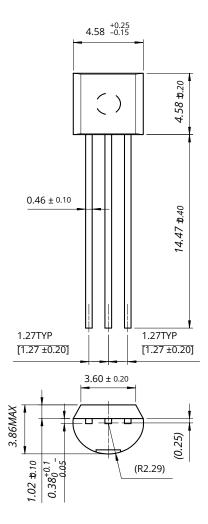


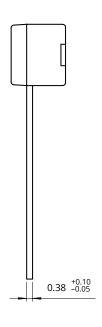
Figure 5. Collector Output Capacitance

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Package Dimensions

TO-92





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